Form PTO-1449 (Rev. 7-80) — U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

LIST OF PRIOR ART CITED BY APPLICANT

(Use several sheets if necessary)

ATTY. DOCKET NO.	SERIAL NO.
	10/713,816
APPLICANT: Johr	
FILING DATE	GROUP: 2877

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
RP	AA	4770895	9/1988	Hartley	427	10	
	AB	5094132	2/1992	Aspnes et al	437	F	
	AC	5526176	6/1996	Welsch et al	356	369	
	AD	5582646	12/1996	Woollam et al	118	708	
	AE	5929995	7/1999	Johr	356	369	
	AF	6537829	6/2003	Yang	356	632	
RP	AG	4933977	6/1990	Southwell	350	164	
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
	AL							
	AM							

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AR		
	AS		

EXAMINER: /Roy Punnoose/ — DATE CONSIDERED: 01/21/2007

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

USCOMM-DC 60-3965

Form 10-6

PLEASE USE THIS FOR PTO FORM 1449 REGARDING ARTICLES

RP

1. "Optical Characterization of Continuous Compositional Gradients in Thin Films by Real Time Spectroscopic Ellipsometry", S. Kim and R.W. Collins, Appl. Phys. Lett. 67 (1995), 3010.

2. "Growth of $Al_xGa_{1-x}As$ Parabolic Quantum Wells by Real-Time Feedback Control of Composition", D.E. Aspnes, W.E. Quinn, M.C. Tamargo, M.A.A. Pudensi, S.A. Schwarz, M.J.S.P. Brasil, R.E. Nahory, and S. Gregory, Appl. Phys. Lett. 60 (1992), 2776.

3. "Real-time Control of the MBE Growth of InGaAs in InP", J.A. Roth, D.H. Chow, G.L. Olson, P.D. Brewer, W.S. Williamson, and B. Johs, J. Crystal Growth 201/202 (1999), 31.

4. "Status of HgCdTe-MBE Technology for Producing Dual-Band Infrared Detectors", R.D. Rajavel, P.D. Brewer, D.M. Jamba, J.E. Jensen, C. LeBeau, G.L. Olson, J.A. Roth, W.S. Williamson, J.W. Bangs, P. Goetz, J.L. Johnson, E.A. Patten, J.A. Wilson, J. Crystal Growth 214/215 (2000), 1100.

5. In Situ Multi-Wavelength Ellipsometric Control of Thickness and Composition for Bragg Reflection Structures", C. Herzinger, B. Johs, P. Chow, D. Reich, G. Carpenter, D. Croswell, and J. Van Hove, Mat. Res. Soc. Symp. Proc. Vol. 406 (1996), 347.

6. "Closed-loop Control of Resonating Tunneling Diode Barier Thickness Using In Situ Spectroscopic Ellipsometry", J.A. Roth, W.S. Williamson, D.H. Chow, G.L. Olson, and B. Johs, J. Vac. Sci. Technol. B 18 (2000), 1439.

7. "In situ Spectral Ellipsometry for Real-Time Measurement and Control", W.M. Duncan and S.A. Henck, Appl. Surf. Sci. 63 (1993), 9.

8. "In Situ Ellipsometric Diagnosis of Multilayer Thin Film Deposition During Sputtering", X. Gao, D.W. Glenn, and J.A. Woollam, Thin Solid Films 313-314 (1998), 511.G.E. Jellison Jr., Thin Solid Films 234 (1993), 416.
data, see references [9,10]).

9. "Spectroscopic Ellipsometry Data Analysis: Measurement Versus Calculated Quantities", G.E. Jellison Jr., Thin Solid Films 313-314 (1998), 511.

10. "Overview of Variable Angle Spectroscopic Ellipsometry (VASE), Part 1: Basic Theory and Typical Applications", J.A. Woollam, B. Johs, C.M. Herzinger, J. Hilfiker, R. Synowicki, and C. L. Bungay, SPIE Critical Reviews Vol. CR72 (1999), 3.

RP

11. "Minimal-data Approaches for Determining Outer-layer

/Roy Punnoose/ 01/21/2007

RP Dielectric Responses of Films From Kinetic Reflectometric and Ellipsometric Measurements", D.E. Aspnes, J. Opt. Soc. Amer. A 10 (1993), 974.

12. "Optical Approaches to Determine Near-Surface Compositions During Epitaxy", D.E. Aspnes, J. Vac. Sci. Technol. A 14 (1996), 960. F.K. Urban III and M.F. Tabet, J. Vac. Sci. Technol. A 11 (1993), 976.

13. "Virtual Interface Method for In Situ Ellipsometry fo Films Grown on Unknown Substrates", F.K. Urban III and M.F. Tabet, J. Vac. Sci. Technol. A 11 (1993), 976.

14. "Real Time Monitoring of the Growth of Transparent Thin Films by Spectroscopic Ellipsometry", M. Kildemo and B. Drevillon, Rev. Sci. Instrum. Vol. 67, No. 5 (1996), 1957.

15. "Characterization of Quasi-Rugate Filters Using Ellipsometric Measurements", A.V. Tikhonravov, M.K. Trubetskov, J. Hrdina, and J. Sobota, Thin Solid Films 277 (1996), 83.

16. "Approximation of Reflection Coefficients for Rapid Real-time Calculation of Inhomogeneous Films", M. Kildemo, O. Hunderi, B. Drevillon, J. Opt. Soc. Am. A 14 (1997), 931.

17. "Real-time In Situ Ellipsometric Control of Antireflection Coatings for Semiconductor Laser Amplifiers Using SiO_x", I-Fan Wu, J.B. Dottellis, M. Dagenais, J. Vac. Sci. Technol. A 11 (1993), 2398.

18. "Real Time Control of Plasma Deposited Optical Filters by Multiwavelength Ellipsometry", T. Heitz, A. Hofrichter, P. Bulkin, and B. Drevillon, J. Vac. Sci. Technol. A 18 (2000), 1303.

19. "Direct Numerical Inversion Method for kinetic Ellipsometry Data. 1. Presentation of the Method and Numerical Evaluation", D. Kouznetsov, A. Hofirchter, and B Drevillon, Appl. Opt. 41 (2002) 4510.

20. "Recherches Sur La Propagation Des Ondes Electromagnetiques Sinusoidales Dans Les Milieuc Stratifies Application Aux Couches Minces", F. Abeles, Ann. De Physique, 5 (1950) 596.

24. Model M2000X, J.A. Woollam Co., Inc., Lincoln, NE USA.

25. "Data Analysis for Spectroscopic Ellipsometry", G.E. Jellison Jr., Thin Solid Films, 234, 1993, 416-422.

26. "In situ and Ex Situ Applications of Spectroscopic RP Ellipsometry", J. A. Woollam, B. Johs, W. McGahan, P. Snyder, J. Hale, H. Yao, Mat. Res. Soc. Proc., Vol 324, 1994, p. 15.

/Roy Punnoose/ 01/21/2007